

ECENCDJ5VU

TVS Diode Array For ESD and Latch-Up Protection

The ECENCDJ5VU TVS array is designed to protect sensitive electronics from damage or latch-up due to ESD and other voltage-induced transient events. It is designed for use in applications where board space is at a premium. Each device will protect up to five lines. It is unidirectional devices and may be used on lines where the signal polarities are above ground. TVS Diode Array For ESD and Latch-Up Protection

Features

- Protects five I/O lines
- Low capacitance
- Working voltages : 5V
- Low leakage current
- Response Time is < 1 ns
- Low operating and clamping voltages
- ROHS compliant
- Meets MSL 1 Requirements
- Solid-state silicon avalanche technology
- Weight 3 milligrams (Approximate)



SOT-563

Main applications

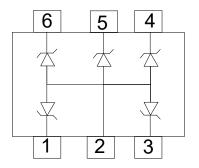
- Cellular Handsets and Accessories
- Cordless Phones
- Personal Digital Assistants (PDA's)
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- MP3 Players

Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)



Device	Qty per Reel	Reel Size
ECENCDJ5VU	3000	7 Inch





Maximum	ratings	(Tamb=25°C	Unless	Otherwise	Specified)	
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Maximum ratings (rand-25 C Oness Otherwise Spec	cincu)		
Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20µs waveform)	Рррр	40	Watts
Peak Pulse Current(tp=8/20µs waveform)	Ірр	3	A
ESD Rating per IEC61000-4-2: Contact		8	W W
Air		15	KV
Lead Soldering Temperature	TL	260 (10 sec.)	°C
Operating Temperature Range	TJ	-55 ~ 150	°C
Storage Temperature Range	Тятд	-55 ~ 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not

normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

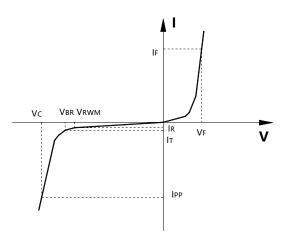
*Other voltages may be available upon request.

1. Non-repetitive current pulse, per Figure 1.

Electric	al characteristics (Tamb=2	25℃ Unless Otherwise Speci	fied)			
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
Vrwm	Reverse Working Voltage				5.0	V
Vbr	Reverse Breakdown Voltage	IT = 1 mA,	6.0			V
Ir	Reverse Leakage Current	$V_{RWM} = 5V,$		0.05	0.5	uA
VF	Diode Forward Voltage	IF = 15mA		0.85	1.2	V
V		$I_{PP} = 1A$, tp =8/20µs,			9.5	V
Vc	Clamping Voltage	$I_{PP} = 3A$, tp =8/20µs,			12	V
I _{PP}	Peak Pulse Current	tp =8/20µs			3	А
CJ	Junction Capacitance	$V_R = 0V, f = 1MHz,$		17	20	pF

Junction capacitance is measured in VR=0V,F=1MHz

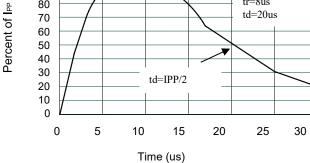
Symbol	Parameter
Vrwm	Working Peak Reverse Voltage
VBR	Breakdown Voltage @ IT
Vc	Clamping Voltage @ IPP
IT	Test Current
Irm	Leakage current at VRWM
Ірр	Peak pulse current
Co	Off-state Capacitance
CJ	Junction Capacitance



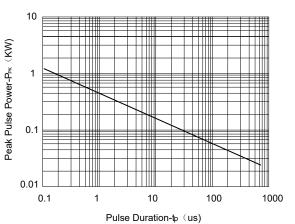


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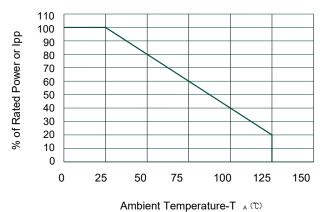
Typical electrical characterist applications



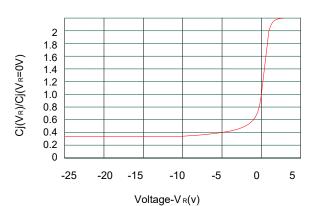
Pulse Waveform







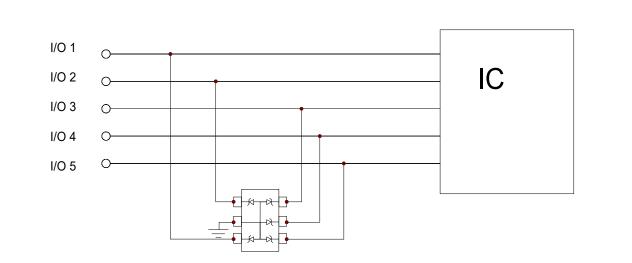
Power Derating Curve



Junction Capacitance vs. Reverse Voltage



Typical applications



Device Connection for Protection of Five Data Lines

The ECENCDJ5VU is designed to protect up to five unidirectional data lines. The device is connected as follows:

Unidirectional protection of five I/O lines is achieved by connecting pins 1, 3, 4, 5 and 6 to the data lines. Pin 2 is connected to ground. The ground connection should be made directly to the ground plane for best results. The path length is kept as short as possible to reduce the effects of parasitic inductance in the board traces.



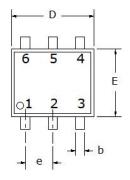
Package Information

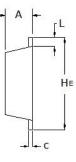
SOT-563

Mechanical Data

Case: SOT-563

Case Material: Molded Plastic. UL Flammability





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Recommended Pad outline

Dim	Millimeters		
	Min	Max	
A	0.525	0.60	
b	0.17	0.27	
с	0.09	0.16	
D	1.50	1.70	
E	1.10	1.30	
e	0.50BSC		
L	0.10	0.30	
HE	1.50	1.70	

